



PATENT
8733.055.00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#5/A

In Re Application of:

Youn Gyoung CHANG et al.

Group Art Unit: 2815

9-11-01

Application No.: 09/466,961

Examiner: Paul E. Brock III. Flowers

Filed: December 20, 1999

For: THIN FILM TRANSISTOR TYPE OPTICAL DETECTING SENSOR

AMENDMENT

Commissioner of Patents
Washington, D.C. 20231

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Sir:

In response to the Examiner's Office Action mailed on May 31, 2001, the following amendments and remarks are respectfully submitted.

IN THE DRAWINGS

Please enter the legend --Related Art-- to Figures 1, 2, and 3.

Change the designation "29" to --21-- in Figure 2.

IN THE SPECIFICATION

On page 7, Paragraph beginning at Line 6, please amend as follows (Exhibit I is a marked up version of the amended Specification paragraph):

As shown in Fig. 4b, a first insulating layer 117, which is preferably one of the group consisting of aluminum oxide (Al_2O_3), silicon oxide (SiO_2) and tantalum oxide (Ta_2O_5), is deposited on the substrate 110 while covering the switch gate 115, the first capacitor electrode 113 and the sensor gate 111. An amorphous silicon layer and an n+ amorphous layer are

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